

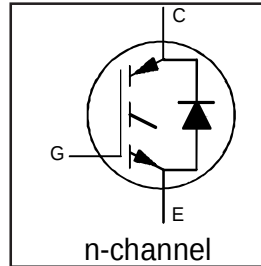
IRG4BC10SD-SPbF IRG4BC10SD-LPbF

INSULATED GATE BIPOLAR TRANSISTOR WITH
ULTRAFAST SOFT RECOVERY DIODE

Standard Speed
CoPack IGBT

Features

- Extremely low voltage drop 1.1Vtyp. @ 2A
- S-Series: Minimizes power dissipation at up to 3 KHz PWM frequency in inverter drives, up to 4 KHz in brushless DC drives.
- Very Tight Vce(on) distribution
- IGBT co-packaged with HEXFRED™ ultrafast, ultra-soft-recovery anti-parallel diodes for use in bridge configurations
- Industry standard D²Pak & TO-262 packages
- Lead-Free



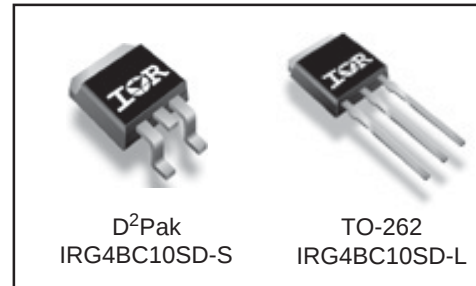
$$V_{CES} = 600V$$

$$V_{CE(on)} \text{ typ.} = 1.10V$$

$$@V_{GE} = 15V, I_C = 2.0A$$

Benefits

- Generation 4 IGBT's offer highest efficiencies available
- IGBT's optimized for specific application conditions
- HEXFRED diodes optimized for performance with IGBT's. Minimized recovery characteristics require less/no snubbing
- Lower losses than MOSFET's conduction and Diode losses



Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	600	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	14	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	8.0	
I_{CM}	Pulsed Collector Current ①	18	
I_{LM}	Clamped Inductive Load Current ②	18	
$I_F @ T_C = 100^\circ C$	Diode Continuous Forward Current	4.0	
I_{FM}	Diode Maximum Forward Current	18	
V_{GE}	Gate-to-Emitter Voltage	± 20	V
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	38	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	15	
T_J	Operating Junction and	-55 to +150	$^\circ C$
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case - IGBT	—	—	3.3	$^\circ C/W$
$R_{\theta JC}$	Junction-to-Case - Diode	—	—	7.0	
$R_{\theta CS}$	Case-to-Sink, flat, greased surface	—	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount ⑤	—	—	80	
$R_{\theta JA}$	Junction-to-Ambient (PCB Mount, steady state)⑥	—	—	40	
Wt	Weight	—	2.0(0.07)	—	g (oz)

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Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage③	600	—	—	V	$V_{GE} = 0V, I_C = 250\mu A$
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.64	—	V/°C	$V_{GE} = 0V, I_C = 1.0mA$
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	—	1.58	1.8	V	$I_C = 8.0A$ $V_{GE} = 15V$
		—	2.05	—		$I_C = 14.0A$ See Fig. 2, 5
		—	1.68	—		$I_C = 8.0A, T_J = 150^\circ\text{C}$
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	6.0		$V_{CE} = V_{GE}, I_C = 250\mu A$
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	—	-9.5	—	mV/°C	$V_{CE} = V_{GE}, I_C = 250\mu A$
g_{fe}	Forward Transconductance④	3.65	5.48	—	S	$V_{CE} = 100V, I_C = 8.0A$
I_{CES}	Zero Gate Voltage Collector Current	—	—	250	μA	$V_{GE} = 0V, V_{CE} = 600V$
		—	—	1000		$V_{GE} = 0V, V_{CE} = 600V, T_J = 150^\circ\text{C}$
V_{FM}	Diode Forward Voltage Drop	—	1.5	1.8	V	$I_C = 4.0A$ See Fig. 13
		—	1.4	1.7		$I_C = 4.0A, T_J = 150^\circ\text{C}$
I_{GES}	Gate-to-Emitter Leakage Current	—	—	± 100	nA	$V_{GE} = \pm 20V$

Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge (turn-on)	—	15	22	nC	$I_C = 8.0A$
Q_{ge}	Gate - Emitter Charge (turn-on)	—	2.42	3.6		$V_{CC} = 400V$ See Fig. 8
Q_{gc}	Gate - Collector Charge (turn-on)	—	6.53	9.8		$V_{GE} = 15V$
$t_{d(on)}$	Turn-On Delay Time	—	76	—	ns	$T_J = 25^\circ\text{C}$
t_r	Rise Time	—	32	—		$I_C = 8.0A, V_{CC} = 480V$
$t_{d(off)}$	Turn-Off Delay Time	—	815	1200		$V_{GE} = 15V, R_G = 100\Omega$
t_f	Fall Time	—	720	1080		Energy losses include "tail" and diode reverse recovery.
E_{on}	Turn-On Switching Loss	—	0.31	—		See Fig. 9, 10, 18
E_{off}	Turn-Off Switching Loss	—	3.28	—	mJ	
E_{ts}	Total Switching Loss	—	3.60	10.9		
E_{ts}	Total Switching Loss	—	1.46	2.6	mJ	$I_C = 5.0A$
$t_{d(on)}$	Turn-On Delay Time	—	70	—	ns	$T_J = 150^\circ\text{C}$, See Fig. 10,11, 18
t_r	Rise Time	—	36	—		$I_C = 8.0A, V_{CC} = 480V$
$t_{d(off)}$	Turn-Off Delay Time	—	890	—		$V_{GE} = 15V, R_G = 100\Omega$
t_f	Fall Time	—	890	—		Energy losses include "tail" and diode reverse recovery.
E_{ts}	Total Switching Loss	—	3.83	—	mJ	
L_E	Internal Emitter Inductance	—	7.5	—	nH	Measured 5mm from package
C_{ies}	Input Capacitance	—	280	—	pF	$V_{GE} = 0V$
C_{oes}	Output Capacitance	—	30	—		$V_{CC} = 30V$ See Fig. 7
C_{res}	Reverse Transfer Capacitance	—	4.0	—		$f = 1.0MHz$
t_{rr}	Diode Reverse Recovery Time	—	28	42	ns	$T_J = 25^\circ\text{C}$ See Fig. 14
		—	38	57		$T_J = 125^\circ\text{C}$
I_{rr}	Diode Peak Reverse Recovery Current	—	2.9	5.2	A	$T_J = 25^\circ\text{C}$ See Fig. 15
		—	3.7	6.7		$T_J = 125^\circ\text{C}$
Q_{rr}	Diode Reverse Recovery Charge	—	40	60	nC	$T_J = 25^\circ\text{C}$ See Fig. 16
		—	70	105		$T_J = 125^\circ\text{C}$
$di_{(rec)M}/dt$	Diode Peak Rate of Fall of Recovery During t_b	—	280	—	A/ μs	$T_J = 25^\circ\text{C}$ See Fig. 17
		—	235	—		$T_J = 125^\circ\text{C}$

Details of note ① through ④ are on the last page

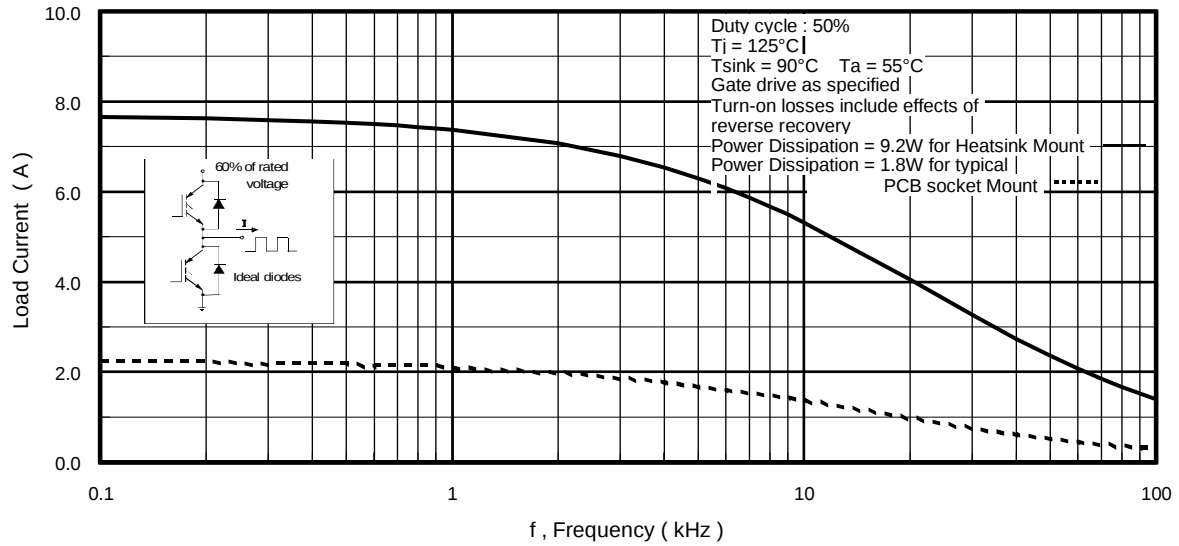


Fig. 1 - Typical Load Current vs. Frequency
 (Load Current = I_{RMS} of fundamental)

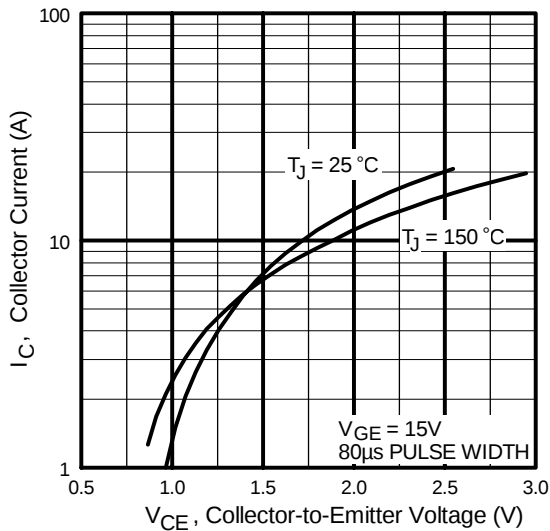


Fig. 2 - Typical Output Characteristics

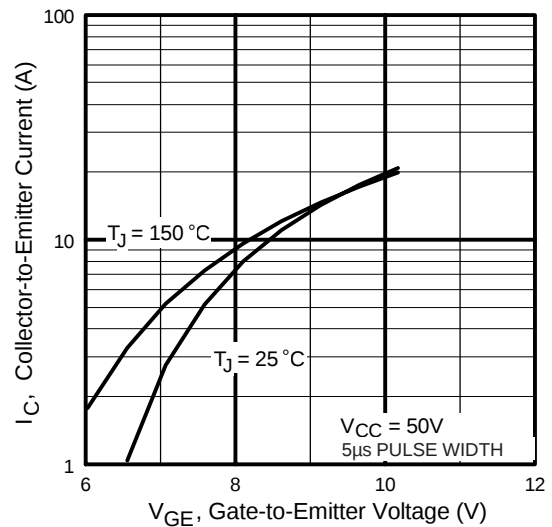


Fig. 3 - Typical Transfer Characteristics

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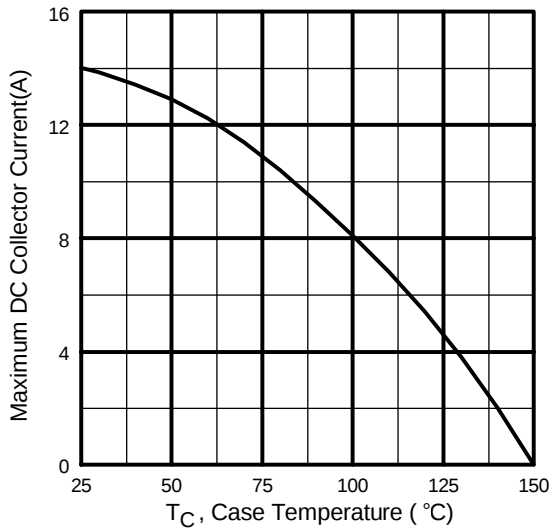


Fig. 4 - Maximum Collector Current vs. Case Temperature

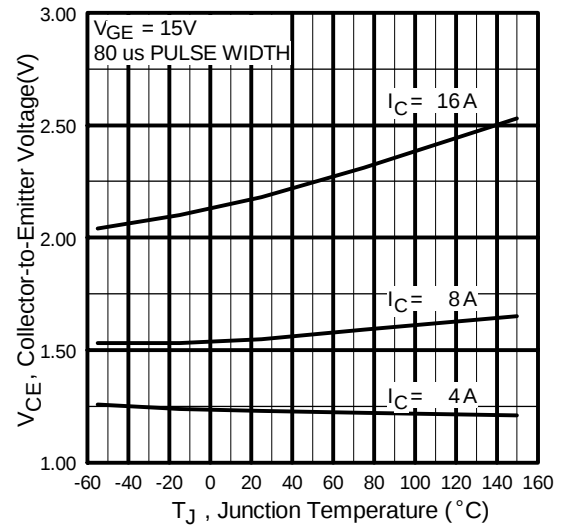


Fig. 5 - Typical Collector-to-Emitter Voltage vs. Junction Temperature

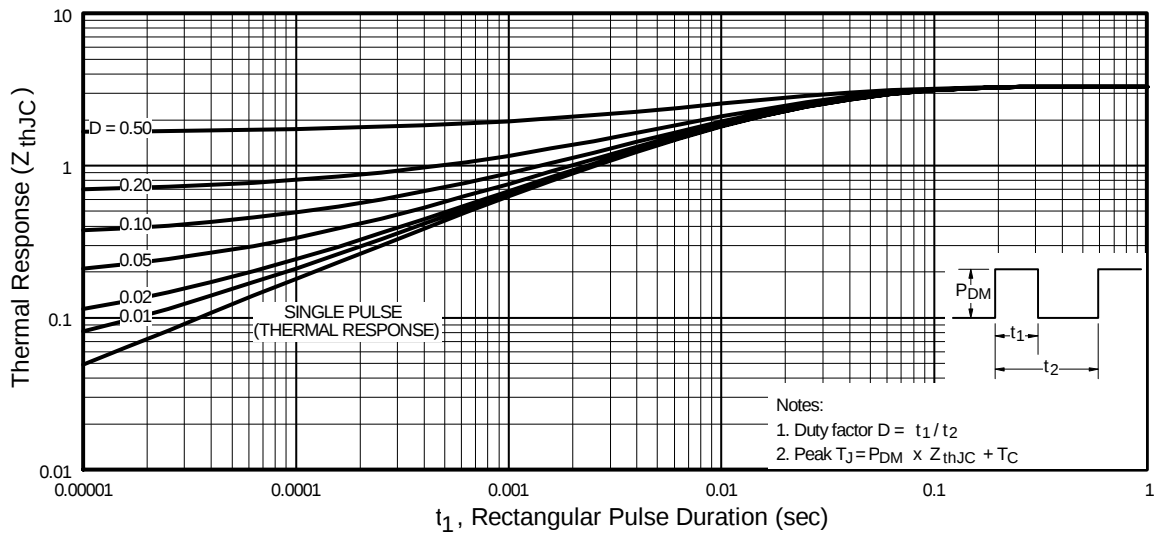


Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

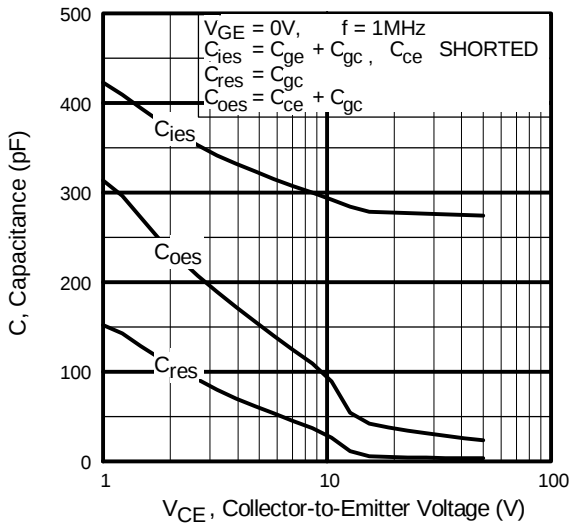


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

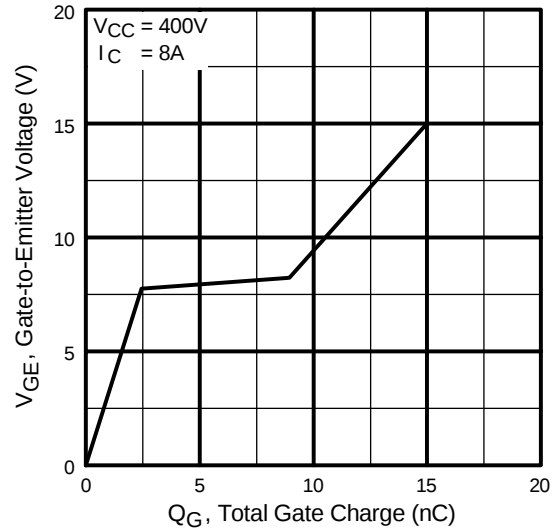


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

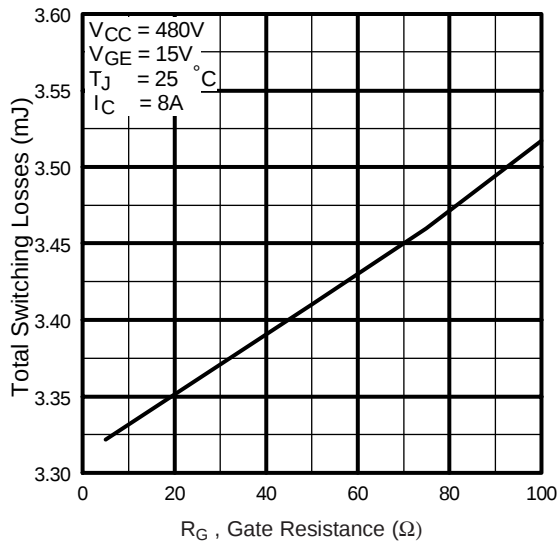


Fig. 9 - Typical Switching Losses vs. Gate Resistance

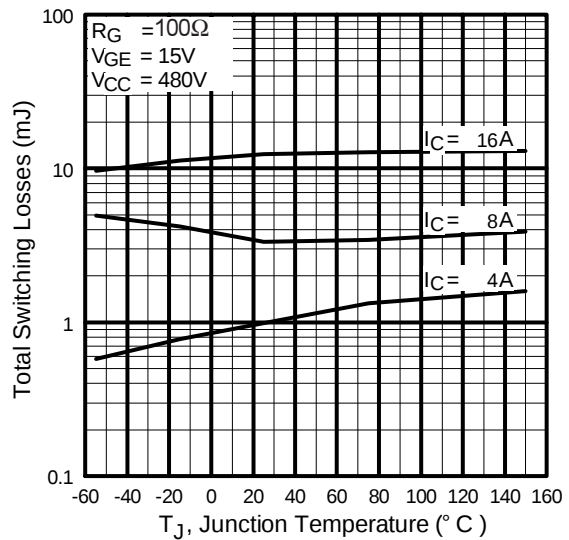


Fig. 10 - Typical Switching Losses vs. Junction Temperature

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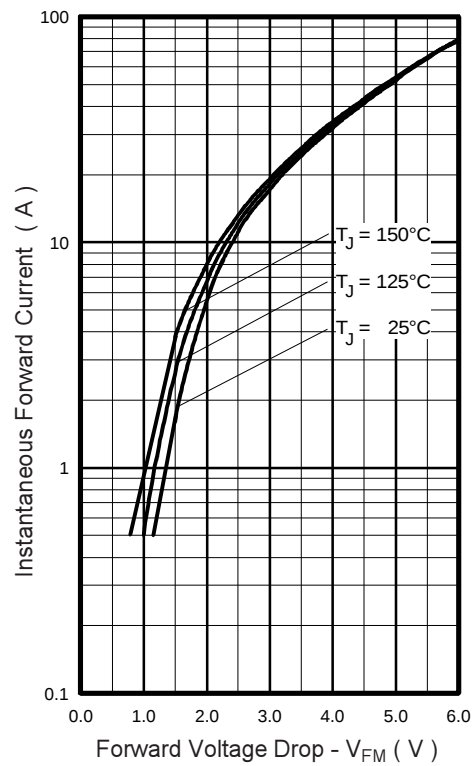
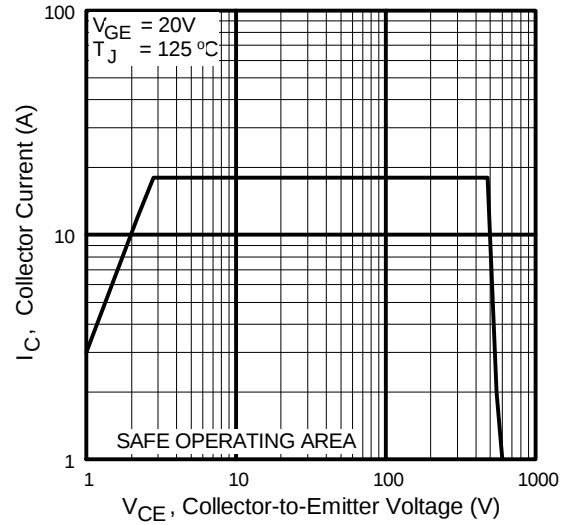
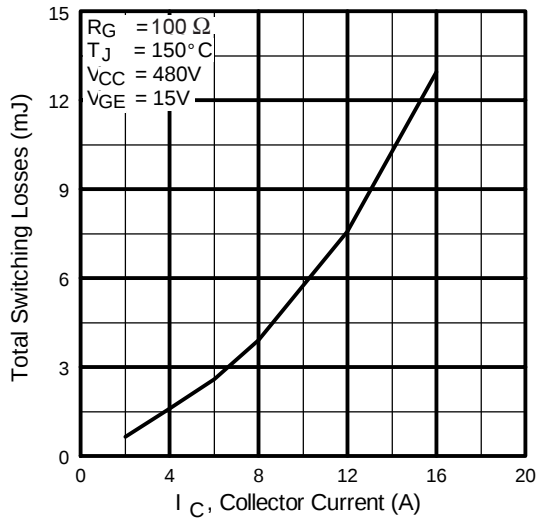


Fig. 13 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

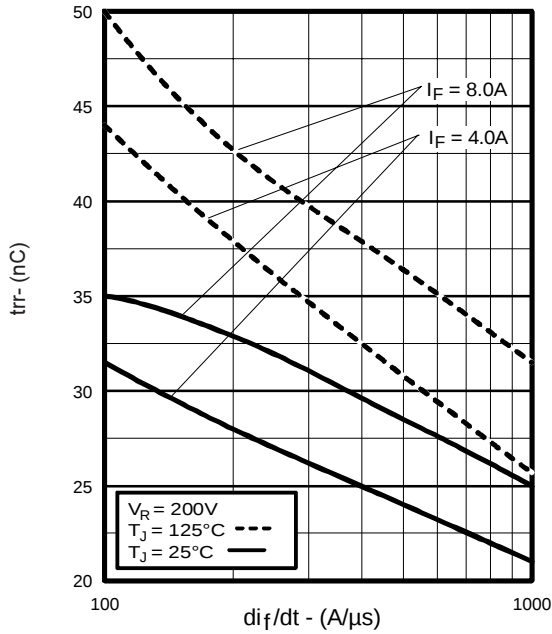


Fig. 14 - Typical Reverse Recovery vs. di_f/dt

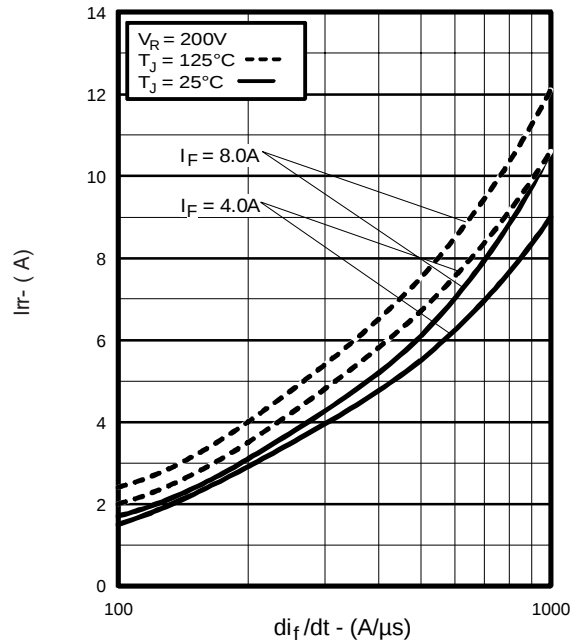


Fig. 15 - Typical Recovery Current vs. di_f/dt

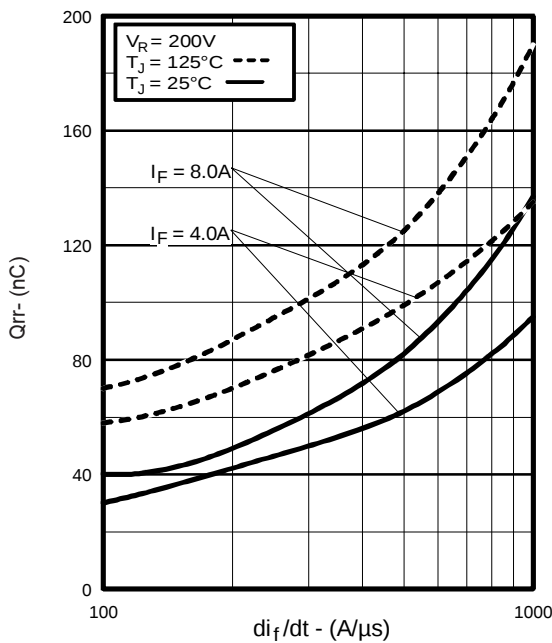


Fig. 16 - Typical Stored Charge vs. di_f/dt

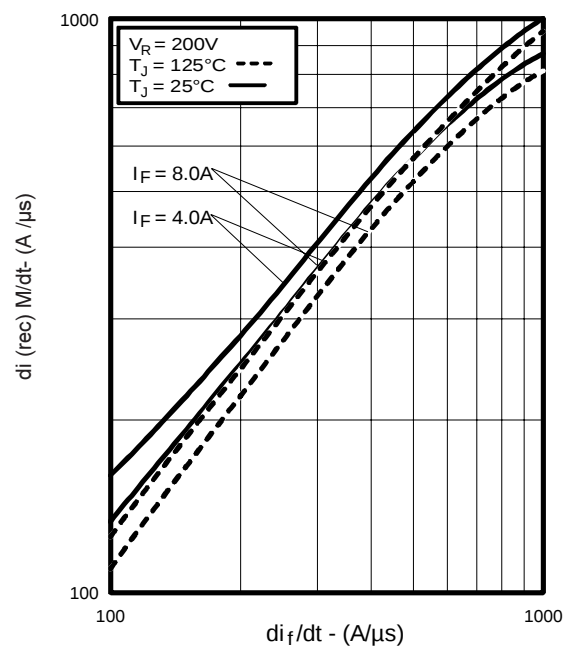


Fig. 17 - Typical $di_{(rec)M}/dt$ vs. di_f/dt

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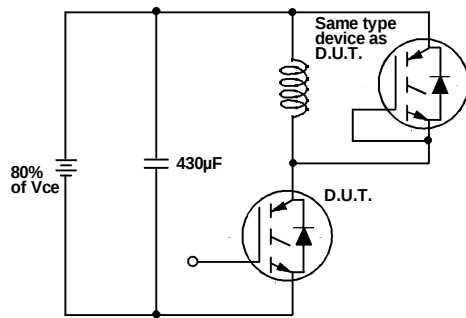


Fig. 18a - Test Circuit for Measurement of I_{LM} , E_{on} , $E_{off}(\text{diode})$, t_{rr} , Q_{rr} , I_{rr} , $t_{d(on)}$, t_r , $t_{d(off)}$, t_f

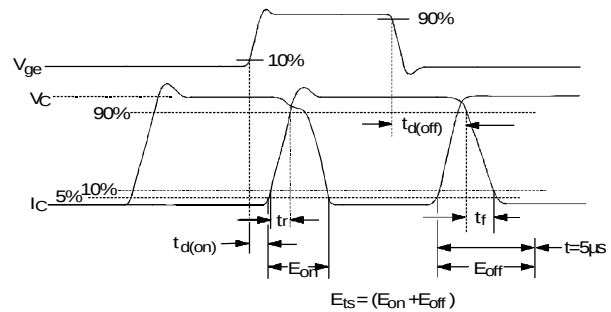


Fig. 18b - Test Waveforms for Circuit of Fig. 18a, Defining E_{off} , $t_{d(off)}$, t_f

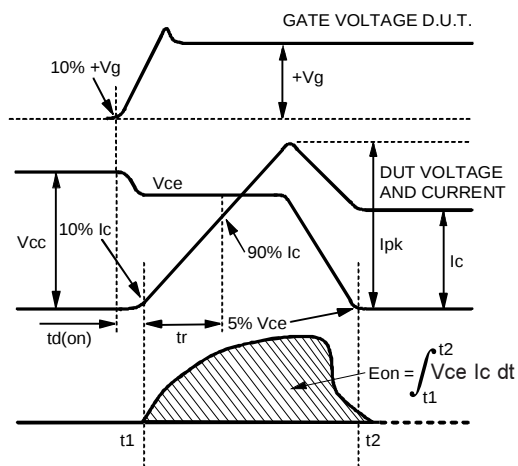


Fig. 18c - Test Waveforms for Circuit of Fig. 18a, Defining E_{on} , $t_{d(on)}$, t_r

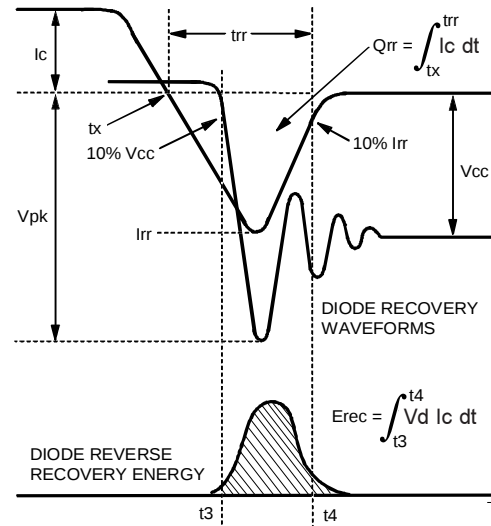


Fig. 18d - Test Waveforms for Circuit of Fig. 18a, Defining E_{rec} , t_{rr} , Q_{rr} , I_{rr}

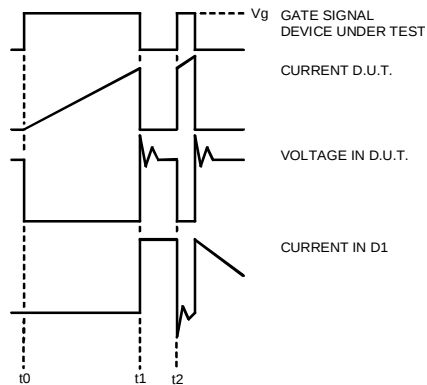


Figure 18e. Macro Waveforms for Figure 18a's Test Circuit

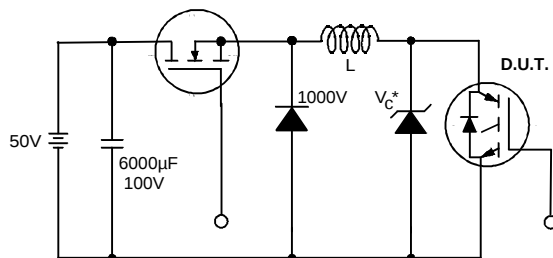


Figure 19. Clamped Inductive Load Test Circuit

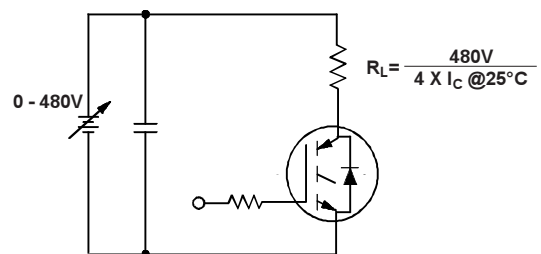
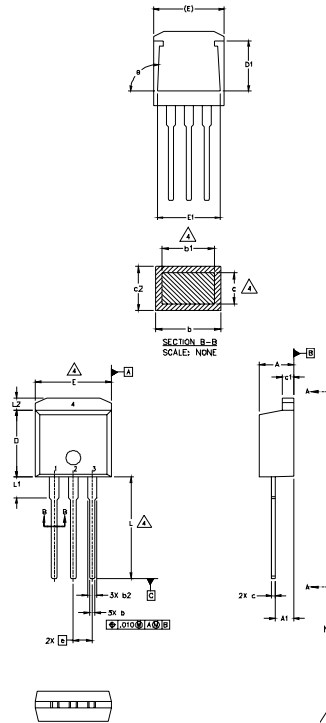


Figure 20. Pulsed Collector Current Test Circuit

TO-262 Package Outline

Dimensions are shown in millimeters (inches)



IRG4BC10SD-S/LPbF

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	4
A1	2.03	2.92	.080	.115	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	
b2	1.14	1.40	.045	.055	4
c	0.38	0.63	.015	.025	
c1	1.14	1.40	.045	.055	
c2	0.43	.063	.017	.029	3
D	8.51	9.65	.335	.380	
D1	5.33		.210		
E	9.65	10.67	.380	.420	
E1	6.22		.245		
e	2.54 BSC		.100 BSC		
L	13.46	14.09	.530	.555	
L1	3.56	3.71	.140	.146	
L2		1.65		.065	

LEAD ASSIGNMENTS

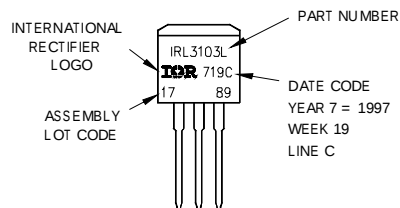
HEXFET	IGBT
1. - GATE	1 - GATE
2. - DRAIN	2 - COLLECTOR
3. - SOURCE	3 - EMITTER
4. - DRAIN	

- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
 2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
 3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [0.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
 4. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
 5. CONTROLLING DIMENSION: INCH.

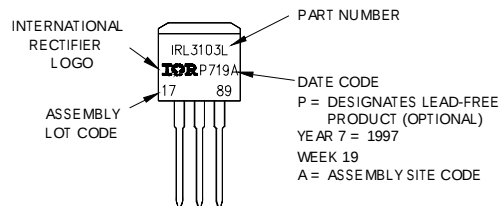
TO-262 Part Marking Information

EXAMPLE: THIS IS AN IRL3103L
LOT CODE 1789
ASSEMBLED ON WW 19, 1997
IN THE ASSEMBLY LINE "C"

Note: "P" in assembly line position indicates "Lead-Free"



OR

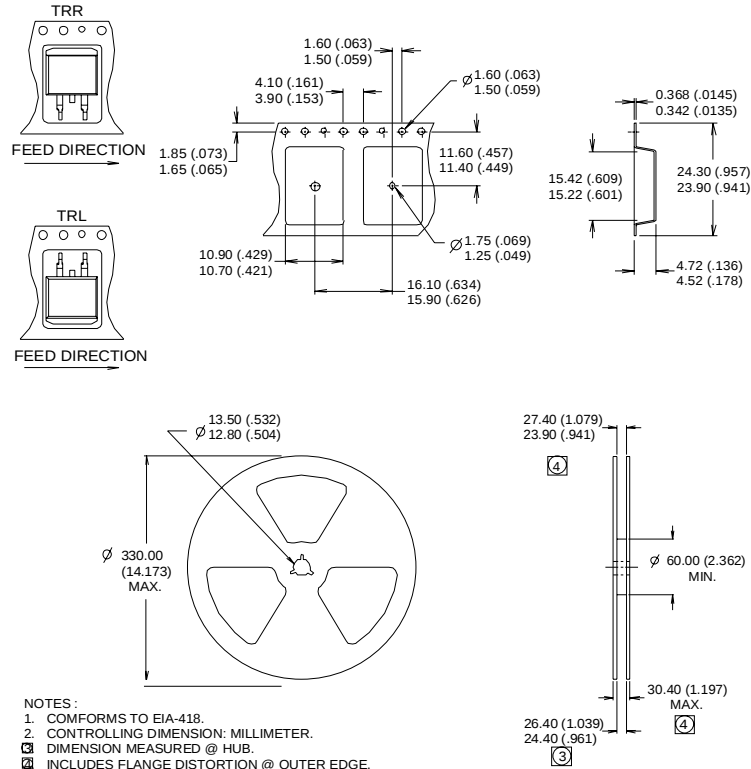


IRG4BC10SD-S/LPbF

D²Pak Tape & Reel Information

Dimensions are shown in millimeters (inches)

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Notes:

- ① Repetitive rating: $V_{GE}=20V$; pulse width limited by maximum junction temperature (figure 20)
- ② $V_{CC}=80\%(V_{CES})$, $V_{GE}=20V$, $L=10\mu H$, $R_G = 100W$ (figure 19)
- ③ Pulse width $\leq 80\mu s$; duty factor $\leq 0.1\%$.
- ④ Pulse width 5.0 μs , single shot.
- ⑤ This only applies to TO-262 package.
- ⑥ This applies to D²Pak, when mounted on 1" square PCB (FR-4 or G-10 Material).
For recommended footprint and soldering techniques refer to application note #AN-994.

Data and specifications subject to change without notice.

This product has been designed and qualified for the Industrial market.

Qualification Standards can be found on IR's Web site.

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Note: For the most current drawings please refer to the IR website at:
<http://www.irf.com/package/>